## N-Channel 30-V (D-S) MOSFET

### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

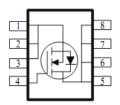
| <b>Typical</b> | Дþ   | plica | atior | ıs: |
|----------------|------|-------|-------|-----|
| .,             | , .P |       | ~     |     |

- White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits

| PRODUCT SUMMARY     |                             |    |  |  |  |
|---------------------|-----------------------------|----|--|--|--|
| V <sub>DS</sub> (V) | I⊳(A)                       |    |  |  |  |
| 30                  | 6.9 @ V <sub>GS</sub> = 10V | 19 |  |  |  |
|                     | $9.8 @ V_{GS} = 4.5V$       | 16 |  |  |  |







| ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED) |                         |                |       |     |  |  |  |
|---|-------------------------|----------------|-------|-----|--|--|--|
| Parameter   | Symbol                  | Limit          | Units |     |  |  |  |
| Drain-Source Voltage  | $V_{DS}$                | 30             | V     |     |  |  |  |
| Gate-Source Voltage   | $V_{GS}$                | ±20            | V     |     |  |  |  |
| Continuous Drain Current <sup>a</sup>                                   | $T_A=25$ °C $T_A=70$ °C | l <sub>D</sub> | 19    |     |  |  |  |
| Continuous Drain Current  |                         | 'D             | 16    | Α   |  |  |  |
| Pulsed Drain Current <sup>b</sup>                                       | I <sub>DM</sub>         | 80             |       |     |  |  |  |
| Continuous Source Current (Diode Conduction) a                          | I <sub>S</sub>          | 5.1            | Α     |     |  |  |  |
| Power Dissipation <sup>a</sup>  | T <sub>A</sub> =25°C    | $P_{D}$        | 3.5   | W   |  |  |  |
| rower Dissipation   | T <sub>A</sub> =70°C    | ' D            | 2     | V V |  |  |  |
| Operating Junction and Storage Temperature Range                        | $T_J,T_stg$             | -55 to 150     | °C    |     |  |  |  |

| THERMAL RESISTANCE RATINGS               |              |                 |         |       |  |  |  |
|--|--------------|-----------------|---------|-------|--|--|--|
| Parameter                                |              | Symbol          | Maximum | Units |  |  |  |
| Maximum Junction-to-Ambient <sup>a</sup> | t <= 10 sec  | $R_{\theta JA}$ | 35      | °C/W  |  |  |  |
| Maximum Junction-to-Ambient              | Steady State | IXOJA           | 81      | C/VV  |  |  |  |

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

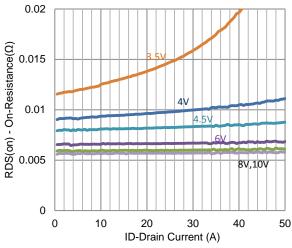
| Parameter                       | Symbol              | Test Conditions   | Min | Тур  | Max  | Unit  |  |
|---------------------------------|---------------------|---|-----|------|------|-------|--|
| Static                          |                     |   |     |      |      |       |  |
| Gate-Source Threshold Voltage   | $V_{GS(th)}$        | $V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$  | 1   |      |      | V     |  |
| Gate-Body Leakage               | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                                 |     |      | ±100 | nA    |  |
| Zero Gate Voltage Drain Current | lane                | $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$                                     |     | 1 1Δ |      | uA    |  |
| Zero Gate Voltage Brain Current | I <sub>DSS</sub>    | $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$         | 25  |      | uA   |       |  |
| On-State Drain Current          | I <sub>D(on)</sub>  | $V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$                                     | 40  |      |      | Α     |  |
| Drain-Source On-Resistance      | r                   | $V_{GS} = 10 \text{ V}, I_D = 17.6 \text{ A}$                                     |     |      | 6.9  | mΩ    |  |
| Dialii-Source Oil-Resistance    | r <sub>DS(on)</sub> | $V_{GS} = 4.5 \text{ V}, I_D = 12.4 \text{ A}$                                    |     |      | 9.8  | 11122 |  |
| Forward Transconductance        | g <sub>fs</sub>     | $V_{DS} = 15 \text{ V}, I_{D} = 17.6 \text{ A}$                                   |     | 30   |      | S     |  |
| Diode Forward Voltage           | $V_{SD}$            | $I_S = 2.6 \text{ A}, V_{GS} = 0 \text{ V}$                                       |     | 0.72 |      | V     |  |
|                                 |                     | Dynamic   |     |      |      |       |  |
| Total Gate Charge               | $Q_g$               | $V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$                                  |     | 20   |      |       |  |
| Gate-Source Charge              | $Q_{gs}$            | $I_{DS} = 13 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 17.6 \text{ A}$ |     | 7.1  |      | nC    |  |
| Gate-Drain Charge               | $Q_{gd}$            | 10 = 17.0 A   |     | 9.2  |      |       |  |
| Turn-On Delay Time              | t <sub>d(on)</sub>  |   |     | 4    |      |       |  |
| Rise Time                       | t <sub>r</sub>      | $V_{DS} = 15 \text{ V}, R_L = 0.9 \Omega, I_D = 17.6 \text{ A},$                  |     | 66   |      | no    |  |
| Turn-Off Delay Time             | $t_{d(off)}$        | $V_{GEN}$ = 10 V, $R_{GEN}$ = 6 $\Omega$  |     | 53   |      | ns    |  |
| Fall Time                       | t <sub>f</sub>      |   |     | 30   |      |       |  |
| Input Capacitance               | C <sub>iss</sub>    |   |     | 1835 |      |       |  |
| Output Capacitance              | C <sub>oss</sub>    | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$                  |     | 315  |      | pF    |  |
| Reverse Transfer Capacitance    | $C_{rss}$           |   |     | 303  |      |       |  |

#### Notes

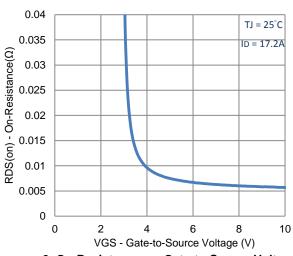
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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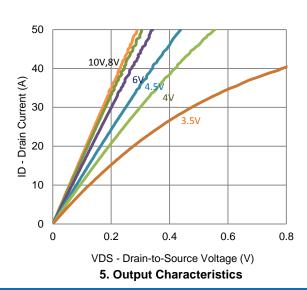
### **Typical Electrical Characteristics**



#### 1. On-Resistance vs. Drain Current

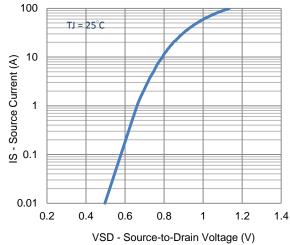


3. On-Resistance vs. Gate-to-Source Voltage

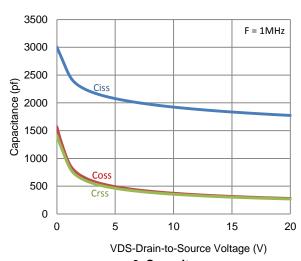


50  $TJ = 25^{\circ}C$ 45 40 ID - Drain Current (A) 35 30 25 20 15 10 5 0 0 1 2 3 5 VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

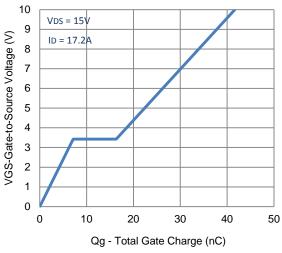


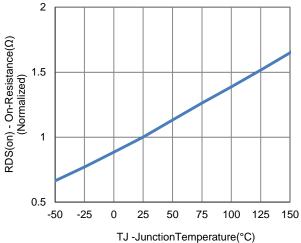
4. Drain-to-Source Forward Voltage



6. Capacitance

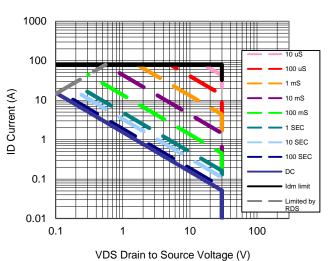
### **Typical Electrical Characteristics**

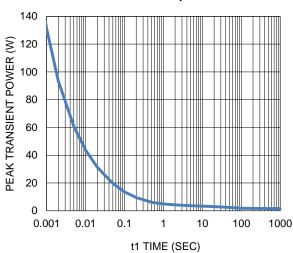




7. Gate Charge

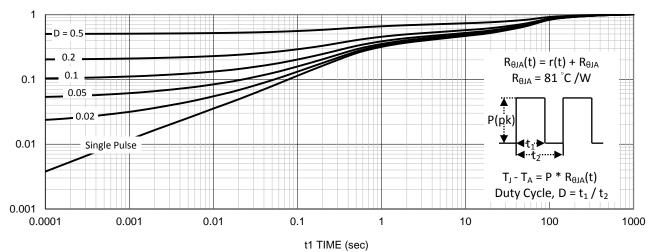






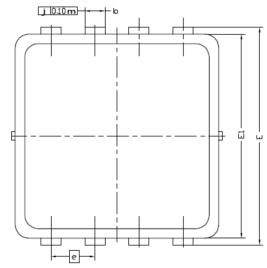
9. Safe Operating Area

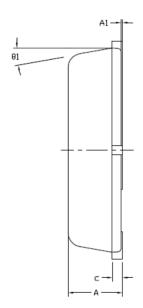
10. Single Pulse Maximum Power Dissipation

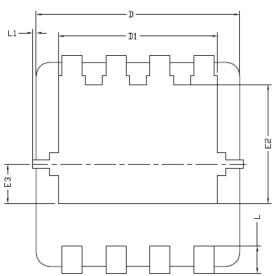


11. Normalized Thermal Transient Junction to Ambient

# Package Information







| птм  | MILLIMETERS |           |       | INCHES    |           |        |  |
|------|-------------|-----------|-------|-----------|-----------|--------|--|
| DIM, | NIM         | NDM       | MAX   | MIN       | NDM       | MAX    |  |
| Α    | 0,700       | 0,80      | 0.900 | 0,0276    | 0,0315    | 0.0354 |  |
| A1   | 0.00        |           | 0,05  | 0,000     |           | 0'005  |  |
| b    | 0.24        | 0.30      | 0.35  | 0.009     | 0.012     | 0.014  |  |
| C    | 0.10        | 0.152     | 0.25  | 0.004     | 0.006     | 0.010  |  |
| D    | 3.00 B2C    |           |       | 0.118 BSC |           |        |  |
| D1   | 2           | 2,35 BSC  |       |           | 0.093 BSC |        |  |
| Ε    | (3          | 3.20 BSC  |       |           | 0.126 BSC |        |  |
| E1   | 3'00 B2C    |           |       | 0,118 BSC |           |        |  |
| E2   | 1.75 BSC    |           |       | 0.069 BSC |           |        |  |
| E3   | 0,          | 0,575 BSC |       |           | 0.023 BSC |        |  |
| е    | 0           | 65 BSC    |       | 0,026 BSC |           |        |  |
| L    | 0,30        | 0,40      | 0,50  | 0,0118    | 0,0157    | 0,0197 |  |
| L1   | 0           |           | 0,100 | 0         |           | 0.004  |  |
| 91   | 0°          | 10°       | 12*   | 0.        | 10°       | 12°    |  |